





N-CHANNEL ENHANCEMENT MODE MOSFET

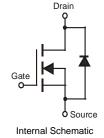
Features

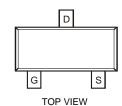
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)







Maximum Ratings @T_A = 25°C unless otherwise specified

Characte	eristic		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	30	V	
Gate-Source Voltage		V _{GSS}	±20	V	
Continuous Drain Current (Note 3)	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I _D	5.8 4.9	А
Pulsed Drain Current	•		I _{DM}	30	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _D	1.4	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	$R_{ heta JA}$	90	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on 1 in FR-4 PCB with 2oz. Copper. The value in any given application depends on the user's specific board design.

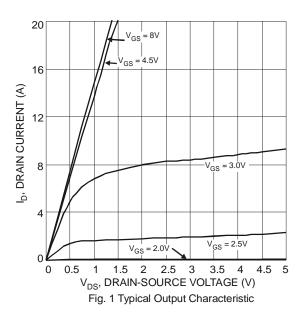


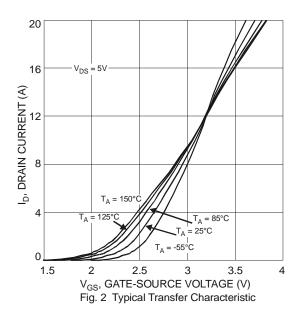
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current TJ = 25°C	I _{DSS}	-	-	1.0	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.5	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
			24	28	$m\Omega$	$V_{GS} = 10V, I_D = 5.8A$	
Static Drain-Source On-Resistance	R _{DS} (ON)	-	33	42		$V_{GS} = 4.5V$, $I_D = 4.8A$	
Forward Transfer Admittance	Y _{fs}	-	10	-	S	$V_{DS} = 5V$, $I_{D} = 5.8A$	
Diode Forward Voltage	V_{SD}	-	0.75	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{iss}	-	386	-	pF	151/1/	
Output Capacitance	Coss	-	44	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	-	39	-	pF	1 – 1.001112	
Gate Resistance	R_g	ı	1.51	ı	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_{g}	-	9.2	-	nC		
Gate-Source Charge	Q_{gs}	-	1.2	-	nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 5.8A$	
Gate-Drain Charge	Q_{gd}	-	1.8	-	nC		
Turn-On Delay Time	t _{D(on)}	-	3.41	-	ns		
Turn-On Rise Time	t _r	-	6.18	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(off)}	-	13.92	-	ns	$R_L = 2.6\Omega$, $R_G = 3\Omega$	
Turn-Off Fall Time	t _f	-	2.84	-	ns		

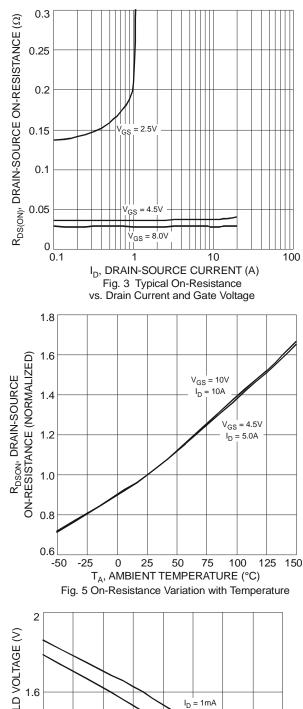
Notes:

4. Short duration pulse test used to minimize self-heating effect.









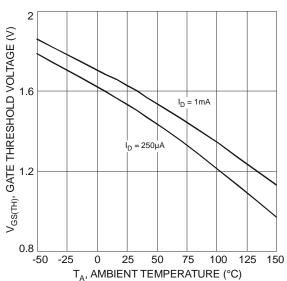
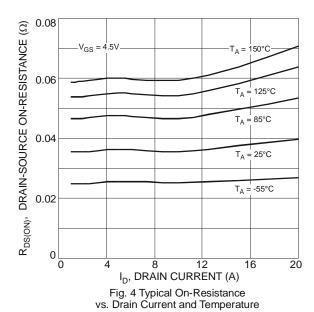
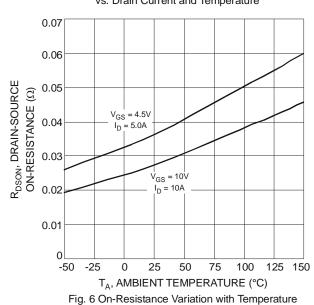
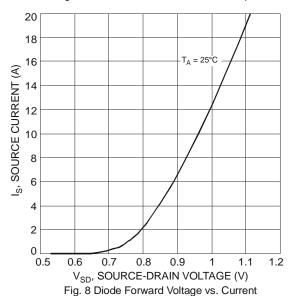


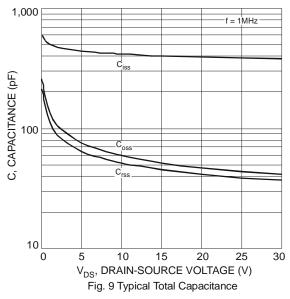
Fig. 7 Gate Threshold Variation vs. Ambient Temperature











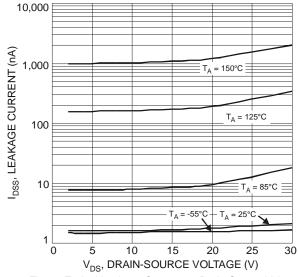


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

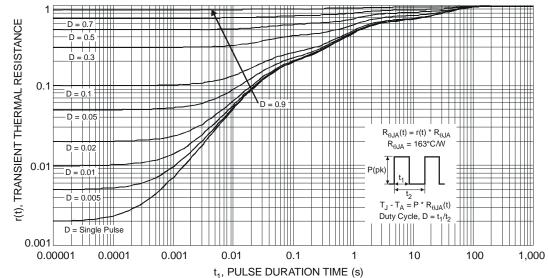


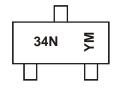
Fig. 11 Transient Thermal Response

Ordering Information (Note 5)

Part Number	Case	Packaging
DMN3404L-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



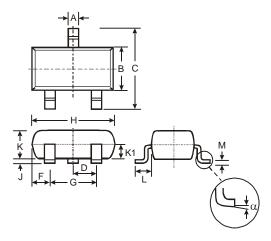
34N = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Х		Υ	2	7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

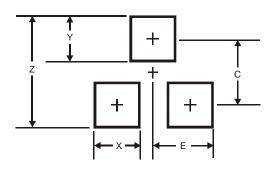


Package Outline Dimensions



	SOT-23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
M	0.085	0.18	0.11				
α	0°	8°	-				
All	All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
C	2.0
F	1 35



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